



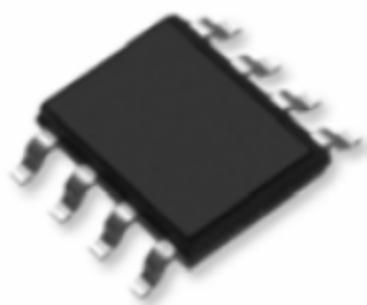
GENERAL FEATURES

- $V_{DS} = -20V$
- $R_{DS(on)} = 68m\Omega @ V_{GS} = -1.8V, I_D = -2A$
- $R_{DS(on)} = 52m\Omega @ V_{GS} = -2.5V, I_D = -4.1A$
- $R_{DS(on)} = 39m\Omega @ V_{GS} = -4.5V, I_D = -4.7A$

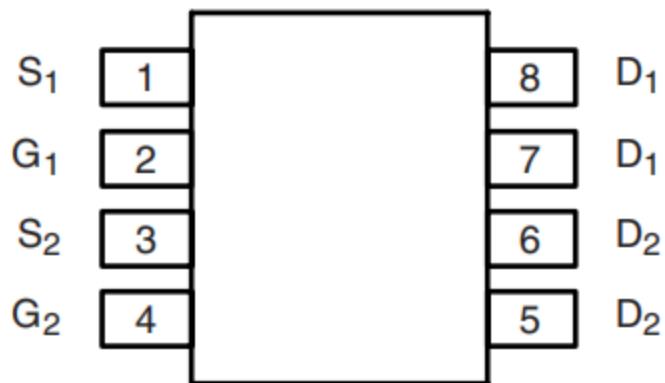
Application

- Load/Power Switching
- Interfacing Switching
- Logic Level Shift

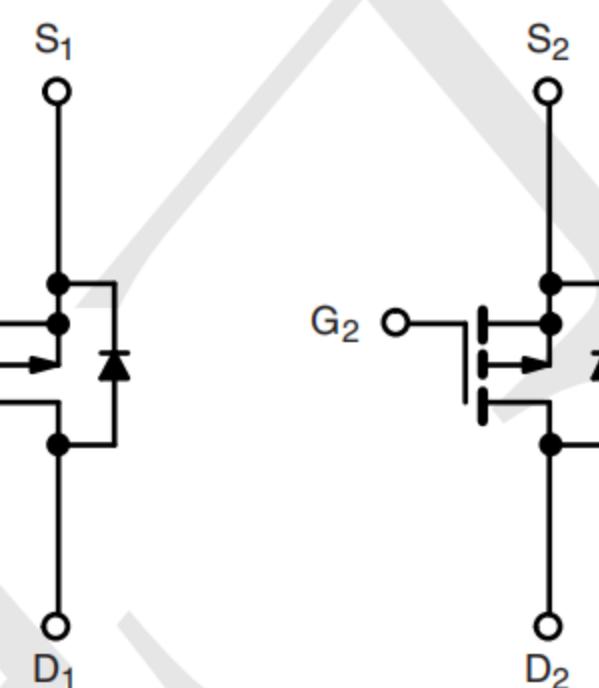
Package and Pin Configuration



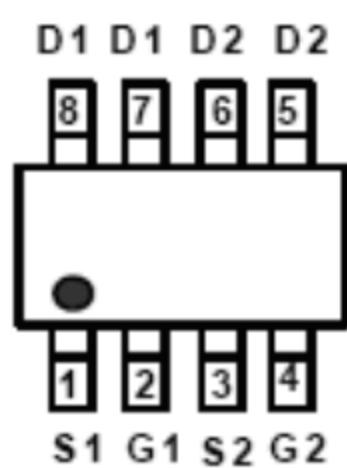
SOP-8 top view



Circuit diagram



Marking:



Absolute Maximum Ratings ($T_A=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Rating	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 12	V
Drain Current (Note 1)	I_D	-4.7	A
Pulsed		-20	
Total Power Dissipation	P_D	1.25	W
@ $TA=75^\circ C$		0.8	
Operating Junction Temperature Range	T_J	-55 to 150	°C



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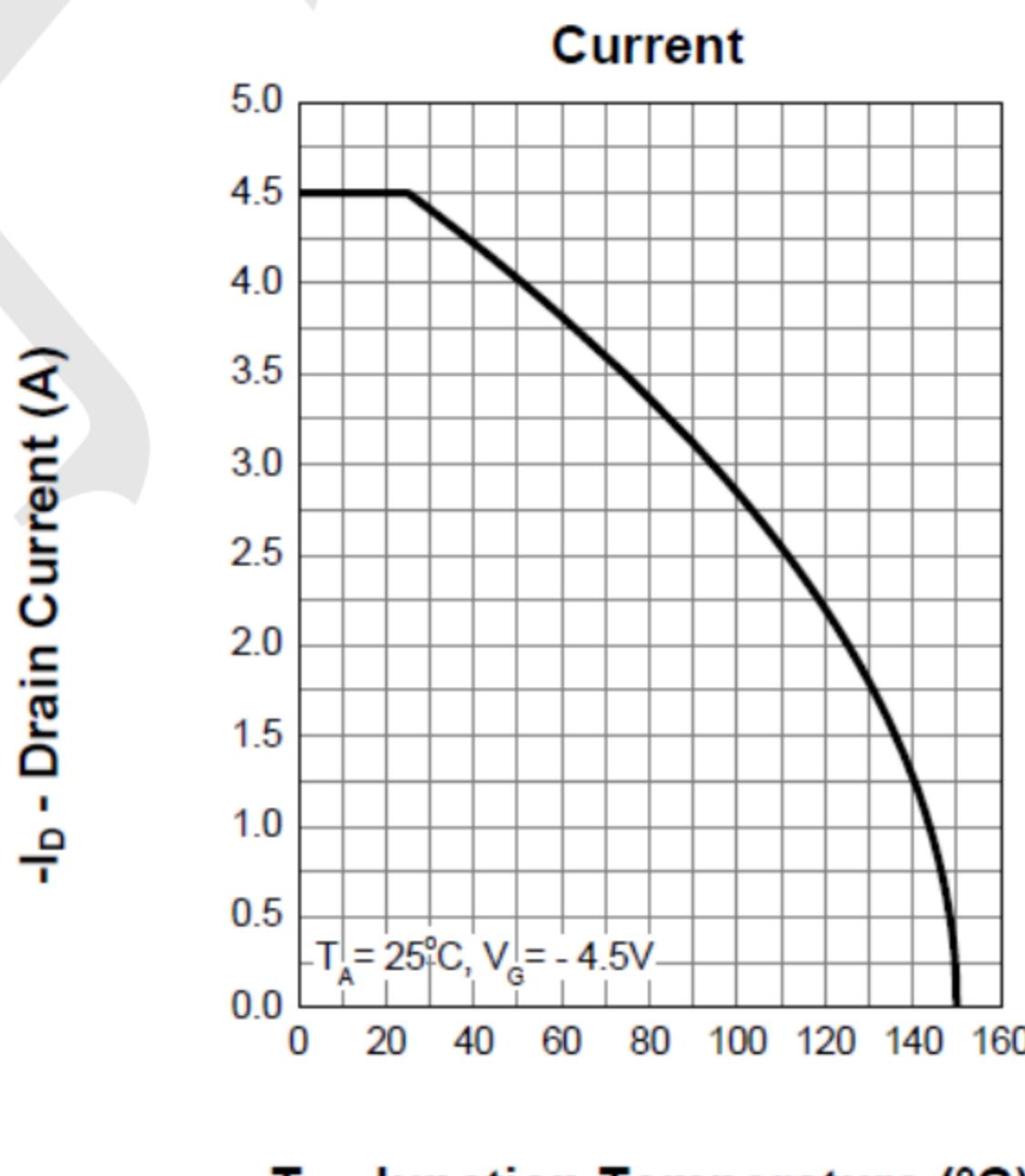
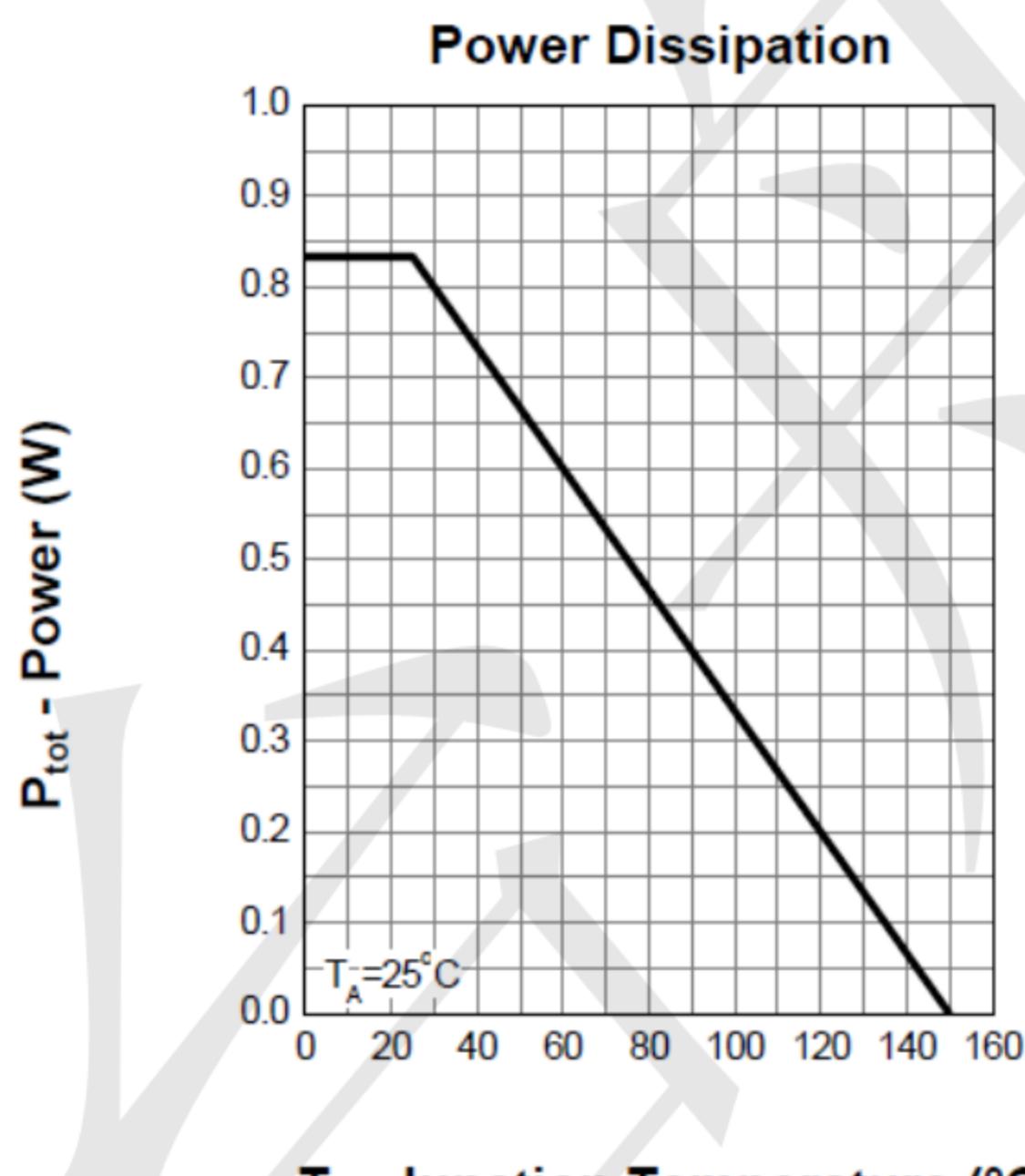
Dual P-Channel Enhancement Mode MOSFET

www.sot23.com.tw

Electrical Characteristics ($T_j=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
OFF CHARACTERISTICS (Note 2)						
BVDSS	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}, V_{GS}=0\text{ V}$	-20	-	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=-16\text{ V}, V_{GS}=0\text{ V}$	-	-	1	μA
IGSS	Gate-Body leakage current	$V_{DS}=0\text{ V}, V_{GS}=\pm 8\text{ V}$	-	-	± 100	μA
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu\text{A}$	-0.4	-	-1	V
$R_{DS(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{GS}=-1.8\text{V}, I_D=-2\text{A}$	-	45	68	$\text{m}\Omega$
		$V_{GS}=-2.50\text{V}, I_D=-4.1\text{A}$		35	52	
		$V_{GS}=-4.5\text{V}, I_D=-4.7\text{A}$	-	30	39	
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=-10\text{V}, f=1\text{MHz}$	-	1020	-	pF
C_{oss}	Output Capacitance		-	191	-	pF
C_{rss}	Reverse Transfer Capacitance		-	140	-	pF
SWITCHING PARAMETERS						
$t_{d(on)}$	Turn-On DelayTime ²	$V_{GS}=-10\text{V}, V_{GEN}=-4.5\text{V}, R_L=10\Omega, R_G=6\Omega, I_D=-1\text{A}$	-	25	50	ns
$t_{d(off)}$	Turn-Off DelayTime		-	71	142	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS}=0\text{V}, I_S=-1$		-	-1.2	V

Typical Electrical and Thermal Characteristics





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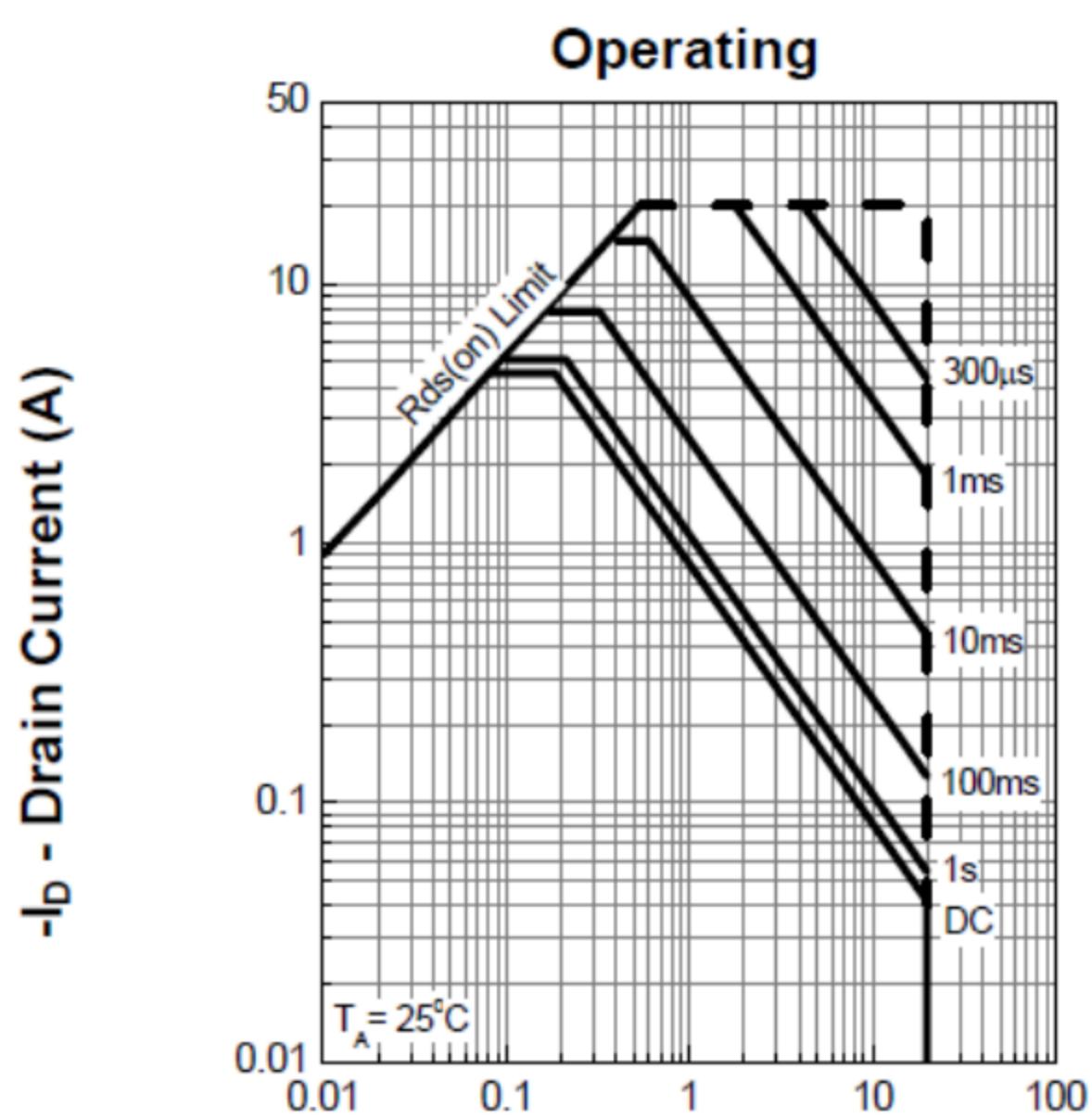
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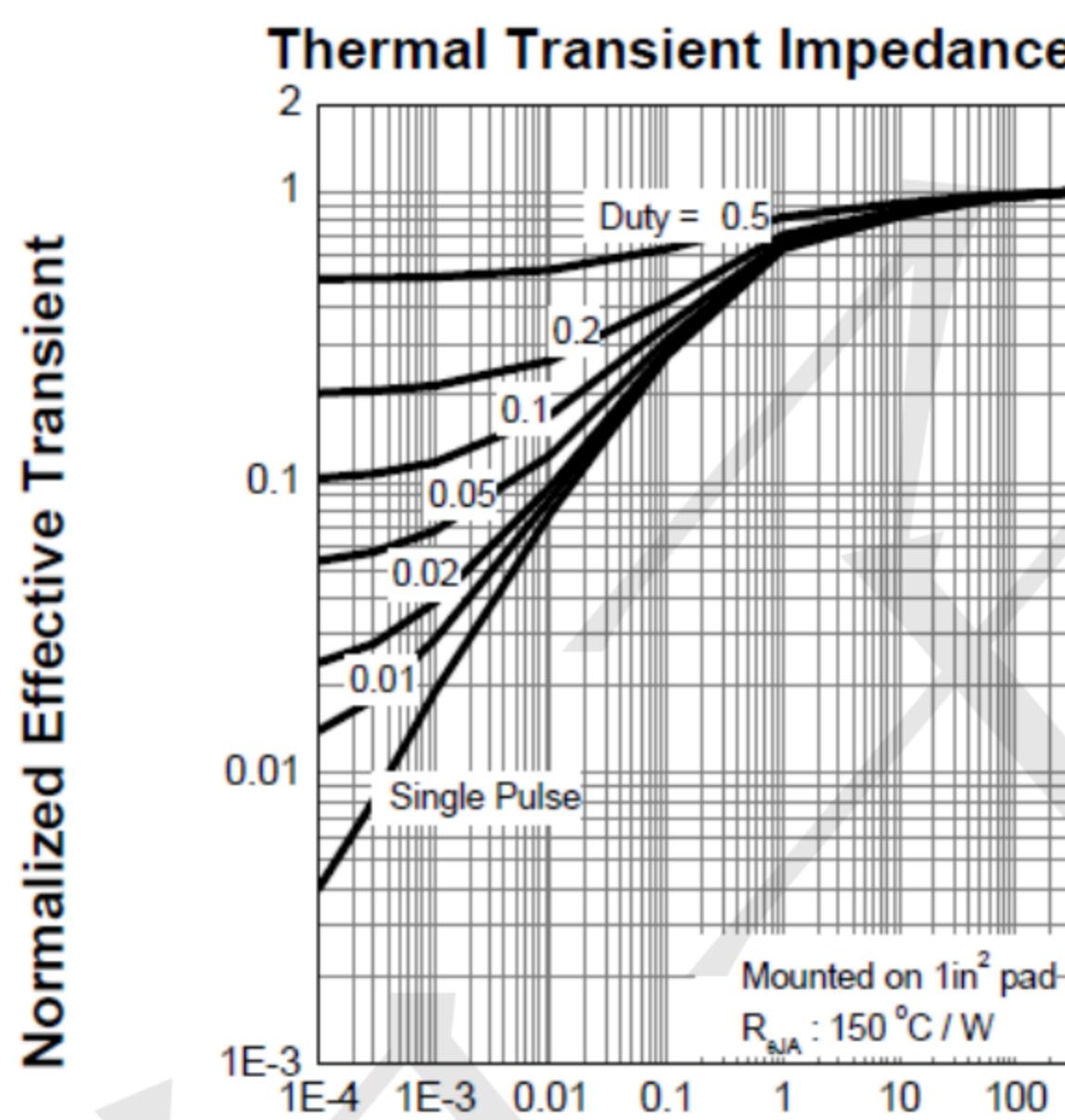
Dual P-Channel Enhancement Mode MOSFET

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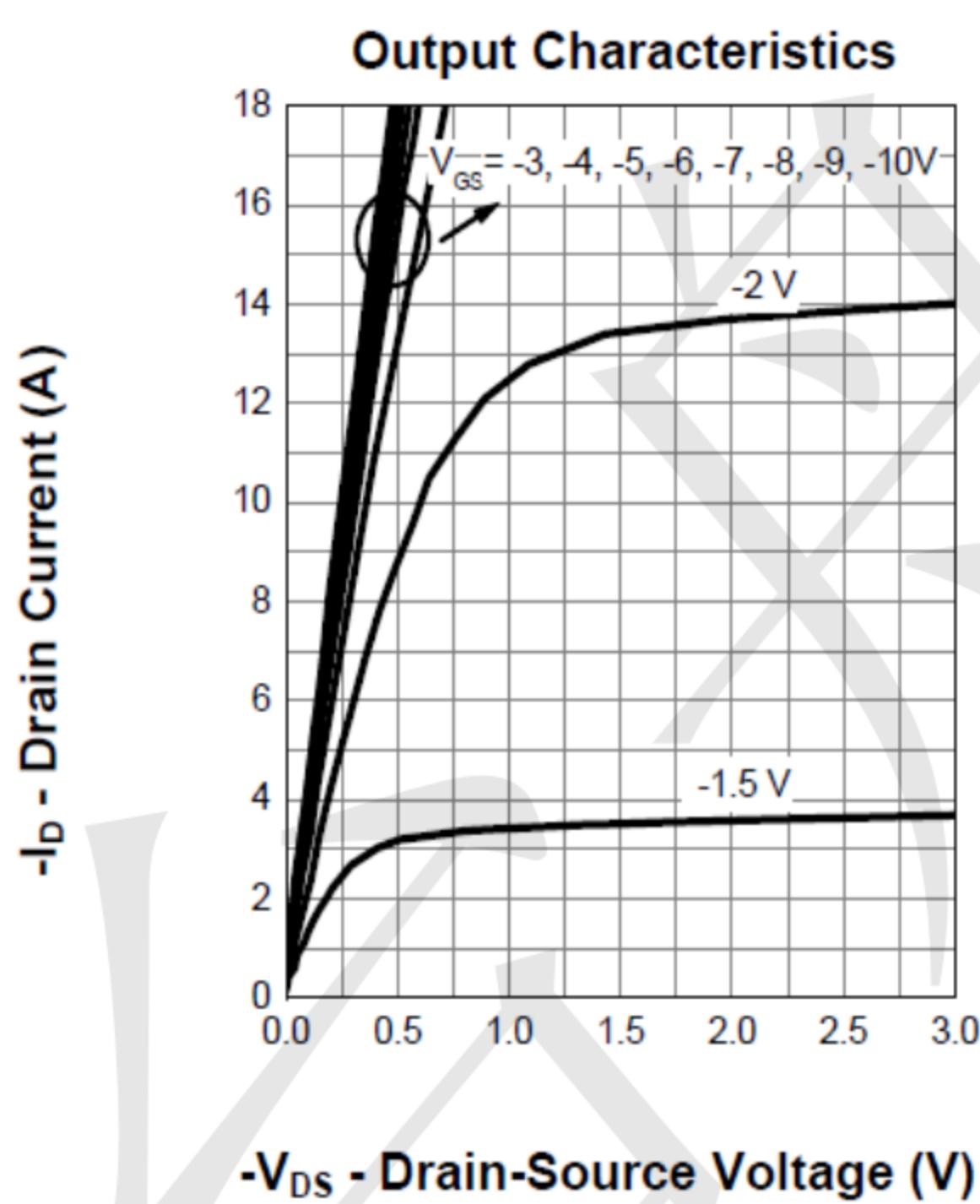
Typical Electrical and Thermal Characteristics



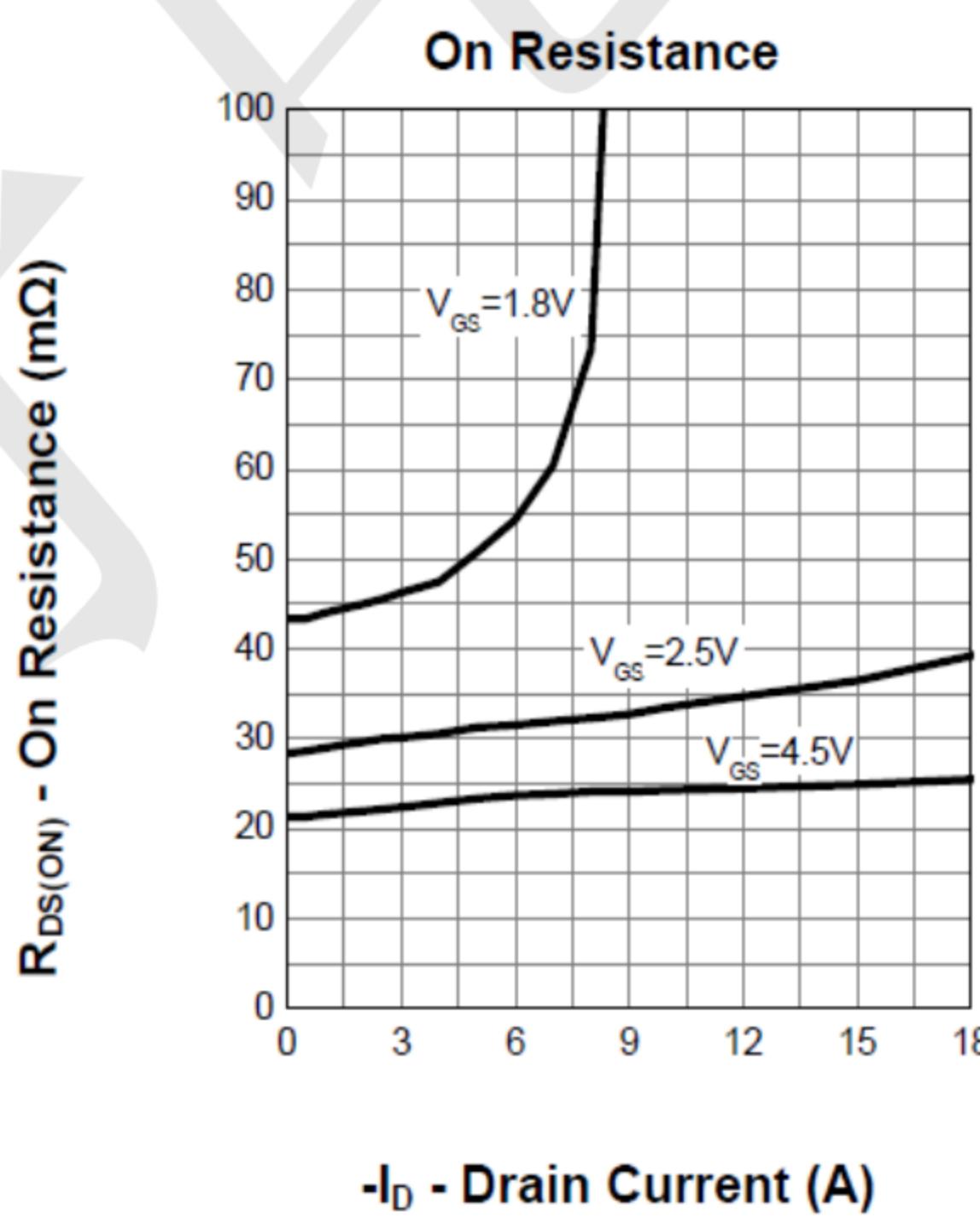
$-V_{DS}$ - Drain-Source Voltage (V)



Square Wave Pulse Duration (sec)

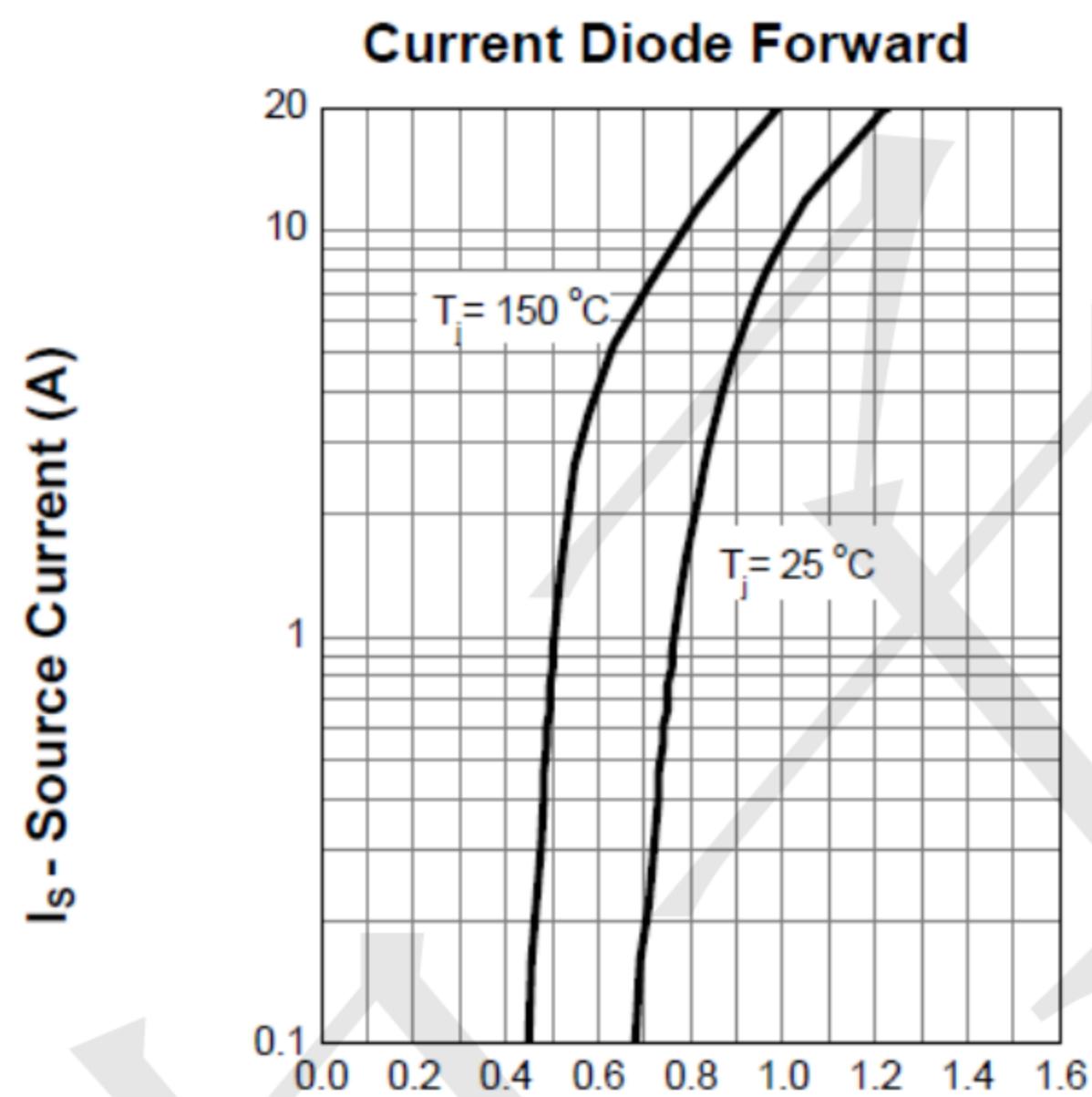
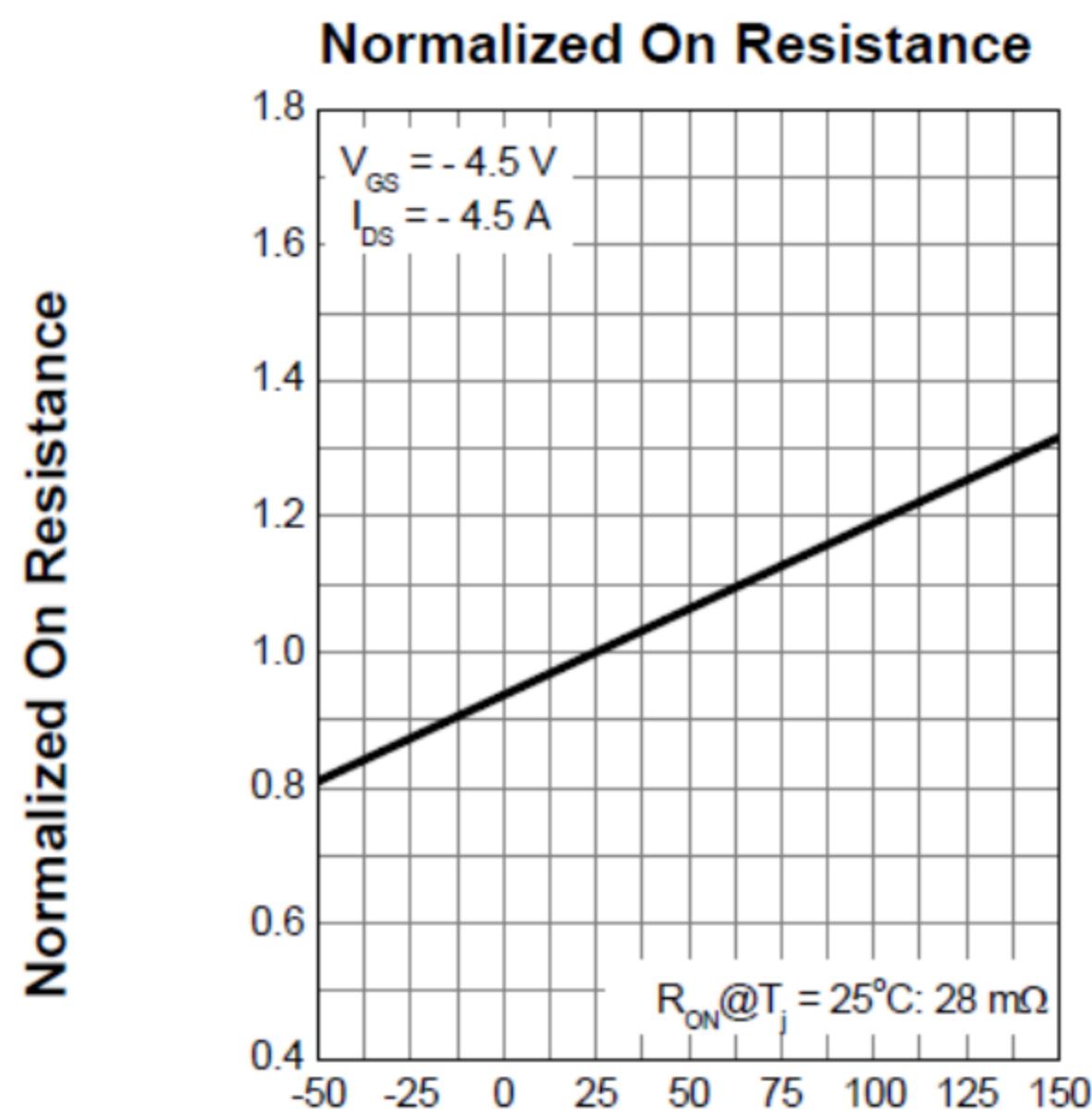


$-V_{DS}$ - Drain-Source Voltage (V)



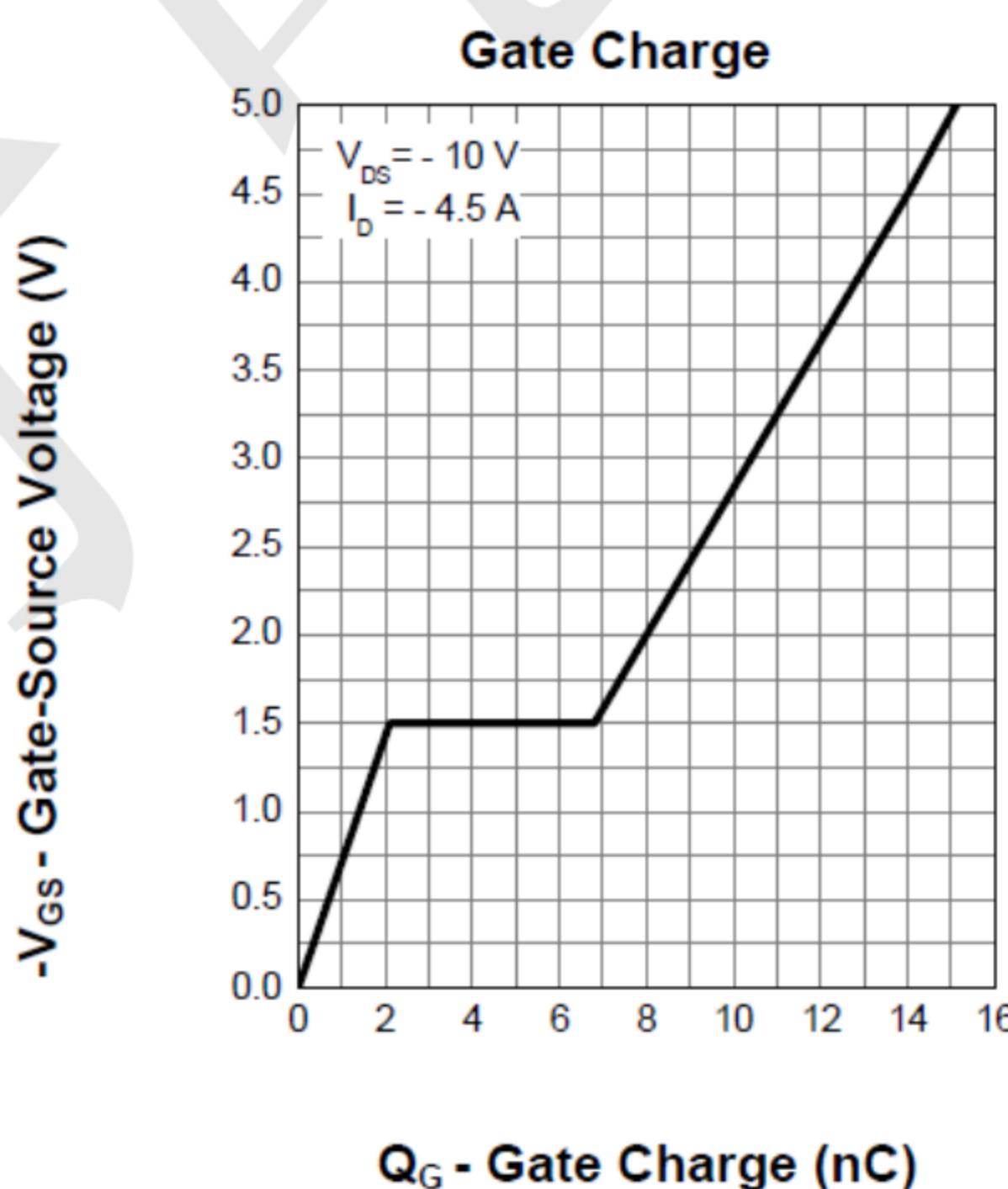
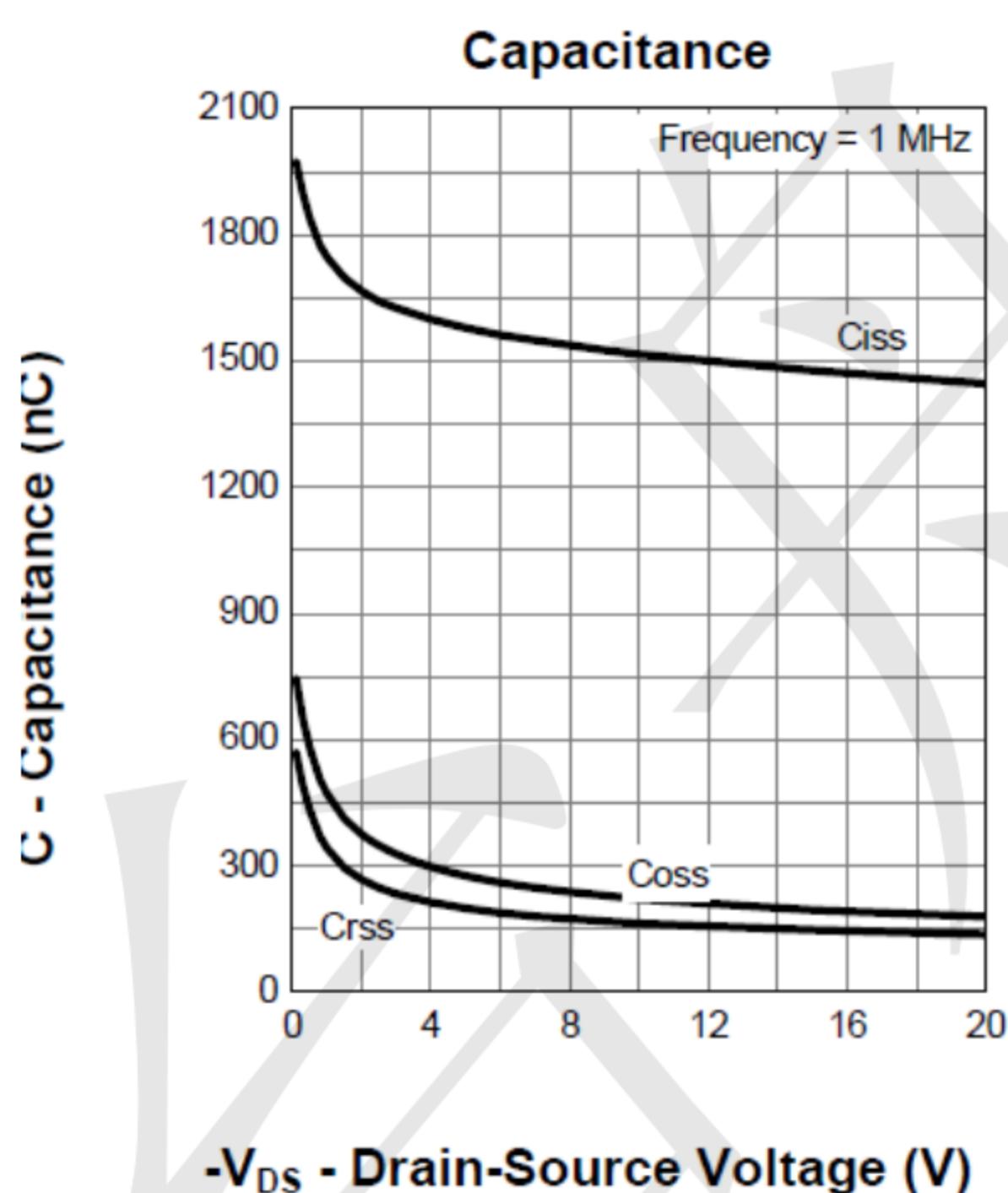
$-I_D$ - Drain Current (A)

Typical Electrical and Thermal Characteristics

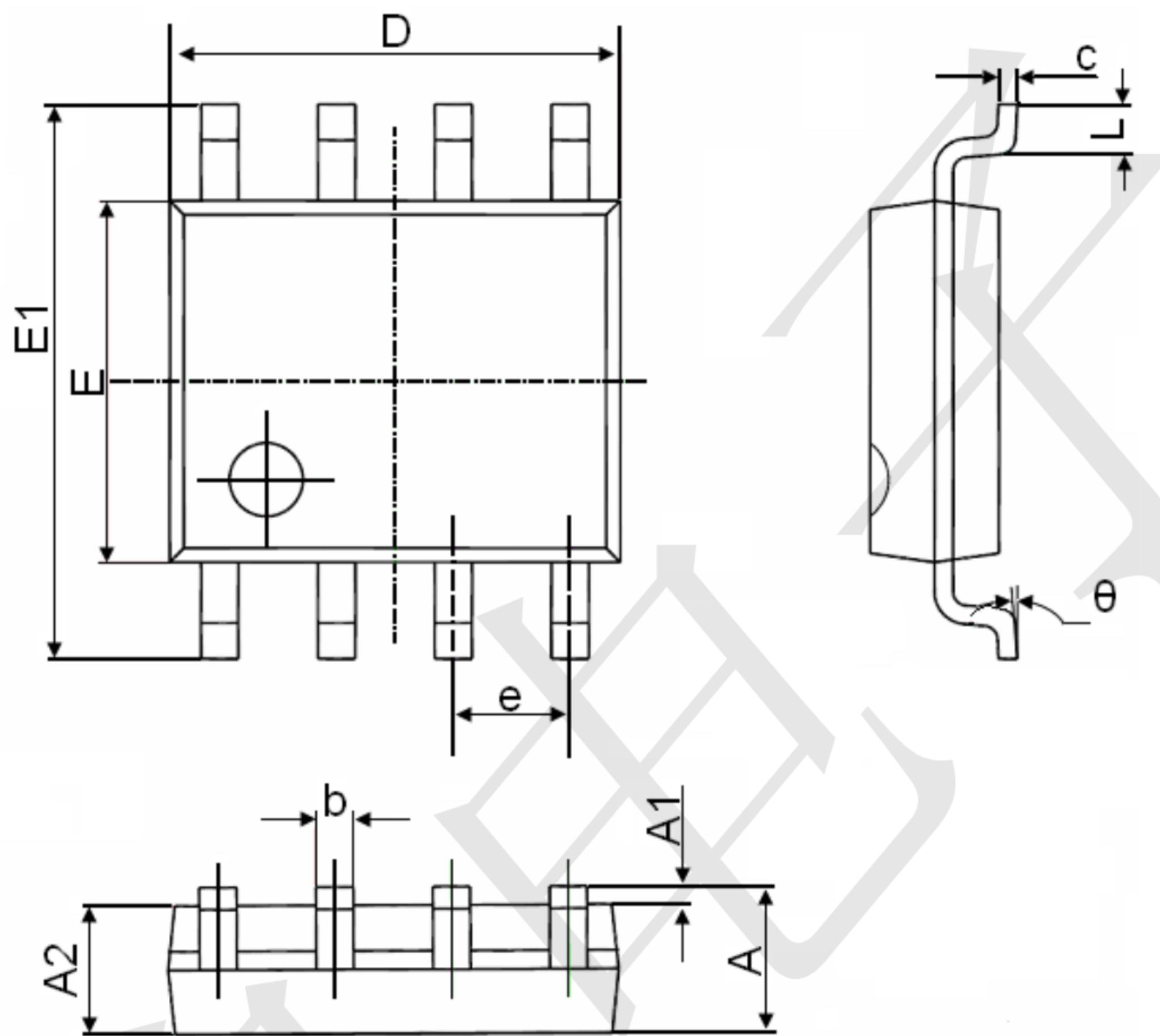


T_j - Junction Temperature ($^\circ\text{C}$)

$-V_{SD}$ - Source-Drain Voltage (V)



SOP-8 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270(BSC)		0.050(BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°